**Amendments to the Claims**

Claims 1-51 (Canceled).

52. (New): A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer having a varied concentration of barium and strontium within the layer, comprising:

providing barium and strontium to a substrate by flowing at least one metal organic precursor to the substrate, and providing titanium to the substrate, and flowing a constant composition oxidizer stream to the substrate, under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate; the barium and strontium being provided to the substrate during all of the deposit of said layer at a substantially constant atomic ratio of barium to strontium; and

during said deposit, changing a rate of flow of the constant composition oxidizer stream to the substrate at least once to effect a change in relative atomic concentration of barium to strontium within the deposited barium strontium titanate comprising dielectric layer.

53. (New): The method of claim 52 comprising changing the rate of flow at least twice.

54. (New): The method of claim 52 comprising providing the barium and strontium to the substrate by flowing at least two metal organic precursors to the substrate, one of the precursors comprising barium, another of the precursors comprising strontium.

55. (New): The method of claim 52 comprising providing the barium and strontium to the substrate by flowing at least two metal organic precursors to the substrate, one of the precursors comprising barium, another of the precursors comprising strontium, the one and the another precursors being fed to the substrate as a mixture from a single flow stream.

56 (New): The method of claim 52 comprising providing the barium and strontium to the substrate during all of the deposit of said layer at substantially constant volumetric flow rates to the substrate.

57. (New): The method of claim 52 wherein the oxidizer is inorganic.

58. (New): The method of claim 52 wherein the oxidizer comprises $NO_x$, where "x" is at least 1.

59. (New): The method of claim 52 wherein the oxidizer comprises NO.

60. (New): A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer having a varied concentration of titanium within the layer, comprising:

providing barium and strontium to a substrate by flowing at least one metal organic precursor to the substrate, and providing titanium to the substrate, and flowing a constant composition oxidizer stream to the substrate, under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate; the barium and strontium being provided to the substrate during all of the deposit of said layer at a substantially constant atomic ratio of barium to strontium; and

during said deposit, changing a rate of flow of the constant composition oxidizer stream to the substrate at least once to effect a change in atomic concentration of titanium relative to barium and strontium within the deposited barium strontium titanate comprising dielectric layer.

61. (New): The method of claim 60 wherein the changing of a rate of flow of the oxidizer to the substrate at least once is also effective to effect a change in relative atomic concentration of barium to strontium within the deposited barium strontium titanate comprising dielectric layer.

62. (New): The method of claim 60 comprising changing the rate of flow at least twice.

63. (New): The method of claim 60 wherein the oxidizer is inorganic.

64. (New): The method of claim 60 wherein the oxidizer comprises $NO_x$, where "x" is at least 1.

65. (New): The method of claim 60 wherein the oxidizer comprises NO.

66. (New): A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer having a varied concentration of barium and strontium within the layer, comprising:

providing barium and strontium to the substrate by flowing at least one metal organic precursor to the substrate, and providing titanium to the substrate, and flowing only a single oxidizer to the substrate, under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate; the barium and strontium being provided to the substrate during all of the deposit of said layer at a substantially constant atomic ratio of barium to strontium; and

during said deposit, changing a rate of flow of the single oxidizer to the substrate at least once to effect a change in relative atomic concentration of barium to strontium within the deposited barium strontium titanate comprising dielectric layer.

67. (New): The method of claim 66 comprising changing the rate of flow at least twice.

68. (New): The method of claim 66 comprising providing the barium and strontium to the substrate by flowing at least two metal organic precursors to the substrate, one of the precursors comprising barium, another of the precursors comprising strontium.

69. (New): The method of claim 66 comprising providing the barium and strontium to the substrate by flowing at least two metal organic precursors to the substrate, one of the precursors comprising barium, another of the precursors comprising strontium, the one and the another precursors being fed to the substrate as a mixture from a single flow stream.

70. (New): The method of claim 66 comprising providing the barium and strontium to the substrate during all of the deposit of said layer at substantially constant volumetric flow rates to the substrate.

71. (New): The method of claim 66 wherein the oxidizer is inorganic.

72. (New): The method of claim 66 wherein the oxidizer comprises $NO_x$, where "x" is at least 1.

73. (New): The method of claim 66 wherein the oxidizer comprises NO.

74. (New): A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer having a varied concentration of titanium within the layer, comprising:

providing barium and strontium to a substrate by flowing at least one metal organic precursor to the substrate, and providing titanium to the substrate, and flowing only a single oxidizer to the substrate, under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate; the barium and strontium being provided to the substrate during all of the deposit of said layer at a substantially constant atomic ratio of barium to strontium; and

during said deposit, changing a rate of flow of the single oxidizer to the substrate at least once to effect a change in atomic concentration of titanium relative to barium and strontium within the deposited barium strontium titanate comprising dielectric layer.

75. (New): The method of claim 74 wherein the changing of a rate of flow of the oxidizer to the substrate at least once is also effective to effect a change in relative atomic concentration of barium to strontium within the deposited barium strontium titanate comprising dielectric layer.

76. (New): The method of claim 74 comprising changing the rate of flow at least twice.

77. (New): The method of claim 74 wherein the oxidizer is inorganic.

78. (New): The method of claim 74 wherein the oxidizer comprises $NO_x$, where "x" is at least 1.

79. (New): The method of claim 74 wherein the oxidizer comprises NO.

80. (New): The method of claim 52 wherein the constant composition oxidizer stream comprises multiple oxidizers.